3.3-V 10-bit Flip Flops with Dual Outputs and 3-state Outputs

# **HITACHI**

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#### **Description**

The HD74ALVCH162820 flip flops are edge triggered D-type flip flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs. A buffered output enable ( $\overline{OE}$ ) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high impedance state. In the high impedance state, the outputs neither load nor drive the bus lines significantly. The high impedance state and increased drive provide the capability to drive bus line without need for interface or pullup components.  $\overline{OE}$  does not affect the internal operations of the flip flops. Old data can be retained or new data can be entered while the outputs are in the high impedance state. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level. All outputs, which are designed to sink up to 12 mA, include 26  $\Omega$  resistors to reduce overshoot and undershoot.

#### **Features**

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical  $V_{OL}$  ground bounce < 0.8 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)
- Typical  $V_{OH}$  undershoot > 2.0 V (@ $V_{CC}$  = 3.3 V, Ta = 25°C)
- High output current  $\pm 12 \text{ mA}$  (@V<sub>CC</sub> = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors
- All outputs have equivalent 26  $\Omega$  series resistors, so no external resistors are required.



#### **Function Table**

Inputs		Output Q		
OEn <sup>*2</sup>	CLK	D		
L	1	Н	Н	
L	$\uparrow$	L	L	
L	L	X	$Q_0^{*1}$	
Н	X	X	Z	

H : High level

L : Low level

X : Immaterial

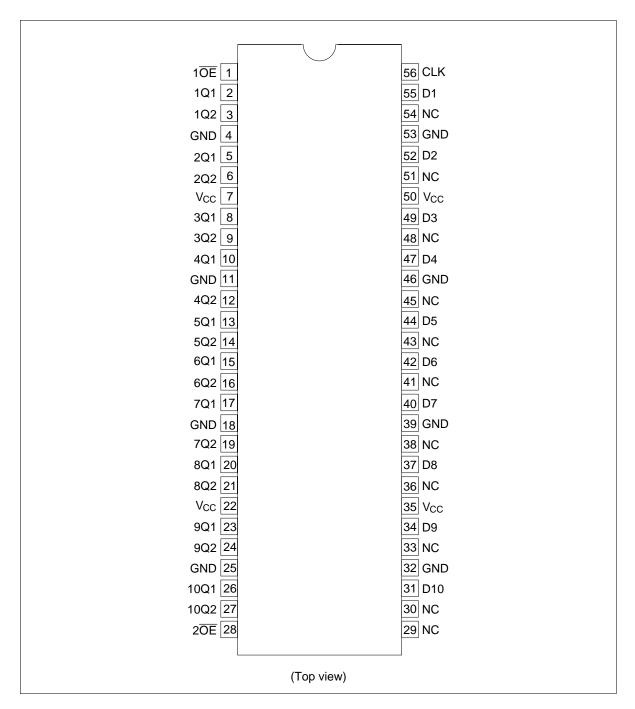
Z : High impedance

↑: Low to high transition

Notes: 1. Output level before the indicated steady state input conditions were established.

2. n = 1, 2

#### **Pin Arrangement**



#### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V <sub>cc</sub>	-0.5 to 4.6	V	_
Input voltage *1	V <sub>i</sub>	-0.5 to 4.6	V	
Output voltage *1, 2	$V_{o}$	–0.5 to $V_{\rm cc}$ +0.5	V	
Input clamp current	I <sub>IK</sub>	-50	mA	V <sub>1</sub> < 0
Output clamp current	I <sub>oK</sub>	±50	mA	$V_{o} < 0 \text{ or } V_{o} > V_{cc}$
Continuous output current	Io	±50	mA	$V_{o} = 0$ to $V_{cc}$
$V_{cc}$ , GND current / pin	$I_{\rm CC}$ or $I_{\rm GND}$	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) *3	P <sub>T</sub>	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

#### Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

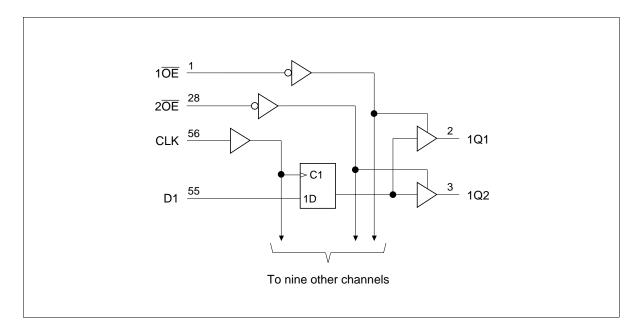
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

#### **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V <sub>cc</sub>	2.3	3.6	V	_
Input voltage	Vı	0	V <sub>cc</sub>	V	
Output voltage	V <sub>o</sub>	0	V <sub>cc</sub>	V	
High level output current	I <sub>OH</sub>	_	-6	mA	V <sub>CC</sub> = 2.3 V
		_	-8		$V_{CC} = 2.7 \text{ V}$
		_	-12		$V_{cc} = 3.0 \text{ V}$
Low level output current	I <sub>OL</sub>	_	6	mA	V <sub>CC</sub> = 2.3 V
		_	8		$V_{CC} = 2.7 \text{ V}$
		_	12		V <sub>CC</sub> = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

## Logic Diagram



## **Electrical Characteristics** ( $Ta = -40 \text{ to } 85^{\circ}\text{C}$ )

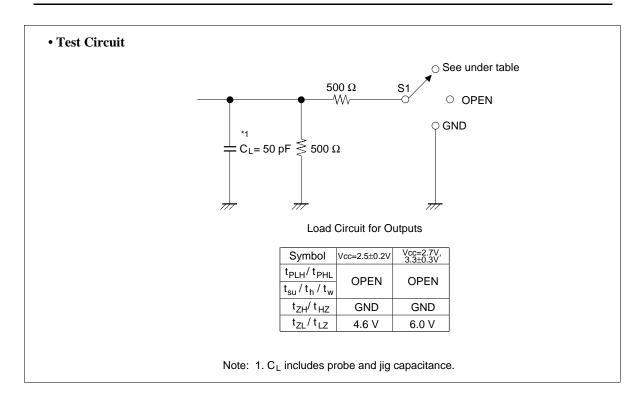
Item	Symbo	I V <sub>cc</sub> (V) *1	Min	Max	Unit	Test Conditions
Input voltage	$V_{\text{IH}}$	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_		
	$V_{IL}$	2.3 to 2.7	_	0.7		
		2.7 to 3.6	_	0.8		
Output voltage	V <sub>OH</sub>	Min to Max	√ V <sub>CC</sub> −0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	1.9	_		$I_{OH} = -4 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		3.0	2.4	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		2.7	2.0	_	<u> </u>	$I_{OH} = -8 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_	<u> </u>	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V <sub>OL</sub>	Min to Max	· —	0.2		$I_{OL} = 100 \mu A$
		2.3	_	0.4	<u> </u>	$I_{OL} = 4 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.55	<u> </u>	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		3.0	_	0.55		$I_{OL} = 6 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		2.7	_	0.6	<u> </u>	$I_{OL} = 8 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.8		$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I <sub>IN</sub>	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
	I <sub>IN (hold)</sub>	2.3	45	_		V <sub>IN</sub> = 0.7 V
		2.3	<b>-45</b>	_		V <sub>IN</sub> = 1.7 V
		3.0	75	_	_	V <sub>IN</sub> = 0.8 V
		3.0	<b>-</b> 75	_		V <sub>IN</sub> = 2.0 V
		3.6	_	±500	_	$V_{IN} = 0 \text{ to } 3.6 \text{ V}$
Off state output curren	t *2 I <sub>OZ</sub>	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply curre	ent I <sub>cc</sub>	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	$\Delta I_{cc}$	3.0 to 3.6	_	750	μΑ	$V_{IN}$ = one input at ( $V_{CC}$ -0.6) V, other inputs at $V_{CC}$ or GND

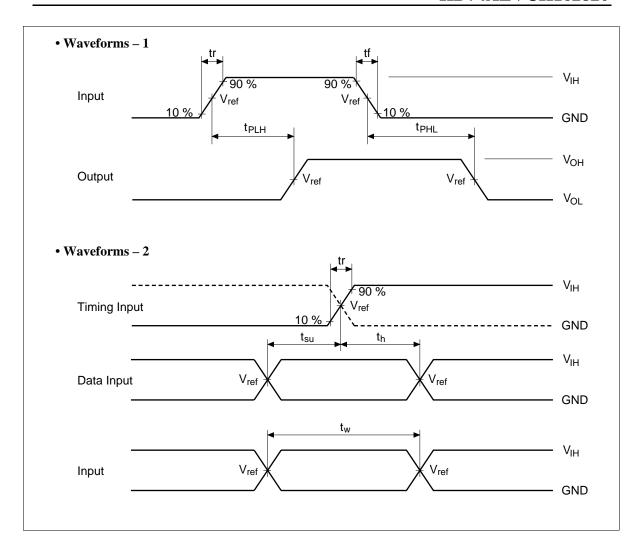
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

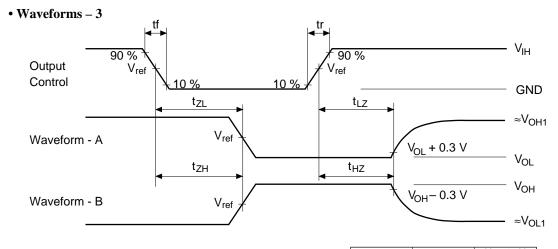
2. For I/O ports, the parameter  $\rm I_{\rm OZ}$  includes the input leakage current.

## **Switching Characteristics** (Ta = -40 to 85°C)

Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f <sub>max</sub>	2.5±0.2	150	_	_	MHz		
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t <sub>PLH</sub>	2.5±0.2	1.0	_	6.4	ns	CLK	Q
	$t_{\text{PHL}}$	2.7	_	_	6.2			
		3.3±0.3	1.0	_	5.4			
Output enable time	t <sub>zH</sub>	2.5±0.2	1.0	_	6.9	ns	ŌĒ	Q
	$\mathbf{t}_{\scriptscriptstyle ZL}$	2.7	_	_	6.8			
		3.3±0.3	1.0	_	5.6	_		
Output disable time	t <sub>HZ</sub>	2.5±0.2	1.3	_	6.2	ns	ŌĒ	Q
	$\mathbf{t}_{LZ}$	2.7	_	_	5.5	<del></del>		
		3.3±0.3	1.0	_	5.0			
Setup time	t <sub>su</sub>	2.5±0.2	1.7	_	_	ns		
		2.7	1.8	_	_			
		3.3±0.3	1.4	_	_	_		
Hold time	t <sub>h</sub>	2.5±0.2	1.1	_	_	ns		
		2.7	1.1	_	_			
		3.3±0.3	1.0	_	_			
Pulse width	t <sub>w</sub>	2.5±0.2	3.3	_	_	ns		
		2.7	3.3	_	_	_		
		3.3±0.3	3.3	_	_	_		
Input capacitance	C <sub>IN</sub>	3.3	_	3.5	_	pF	Control in	puts
		3.3	_	6.0	_		Data inpu	ts
Output capacitance	Co	3.3	_	7.0	_	pF		







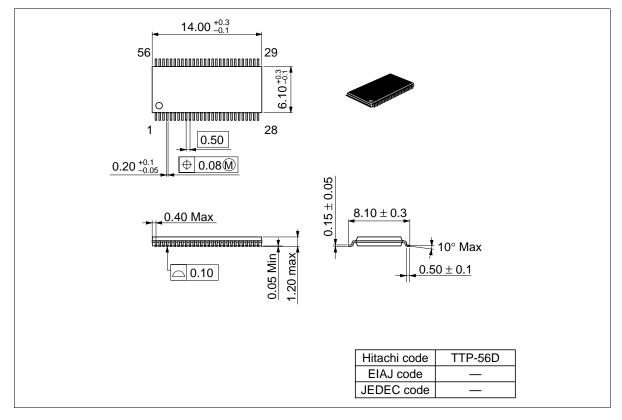
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V <sub>IH</sub>	2.3 V	2.7 V
V <sub>ref</sub>	1.2 V	1.5 V
V <sub>OH1</sub>	2.3 V	3.0 V
V <sub>OL1</sub>	GND	GND

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Zo = 50  $\Omega$ , tr  $\leq$  2.5 ns, tf  $\leq$  2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

## **Package Dimensions**

Unit: mm



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